

# **CR05BS-8**

## **Thyristor**

Low Power Use

REJ03G0347-0200 Rev.2.00 Mar 22, 2007

#### **Features**

•  $I_{T(AV)}: 0.1 A$  $V_{DRM}$ : 400 V  $I_{GT}$ : 100  $\mu A$ 

Non-Insulated Type

Planar Passivation Type

Completed Pb free product

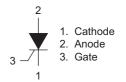
#### **Outline**

RENESAS Package code: PRSS0004ZA-A (Package name:MPAK)



RENESAS Package code: PLSP0003ZA-A (Package name:SC-59)





### **Applications**

Strobe flasher

### **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
Faranietei	Syllibol	8	Oilit	
Repetitive peak reverse voltage	$V_{RRM}$	400	V	
Non-repetitive peak reverse voltage	$V_{RSM}$	500	V	
DC reverse voltage	V <sub>R(DC)</sub>	320	V	
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	400	V	
DC off-state voltage <sup>Note1</sup>	$V_{D(DC)}$	320	V	

#### CR05BS-8

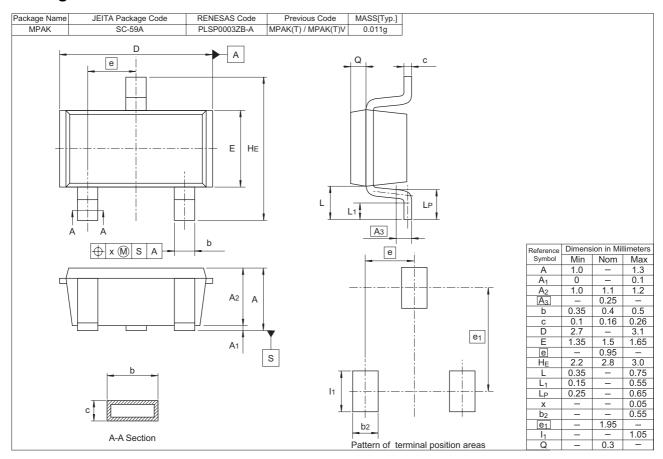
Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	0.15	Α	
Average on-state current	I <sub>T (AV)</sub>	0.1	А	Commercial frequency, sine half wave 180° conduction, Ta = 55°C
Surge on-state current	I <sub>TSM</sub>	10	A	60Hz sine half wave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	0.4	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	0.1	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.01	W	
Peak gate forward voltage	$V_{FGM}$	6	V	
Peak gate reverse voltage	$V_{RGM}$	6	V	
Peak gate forward current	I <sub>FGM</sub>	0.1	Α	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	11	mg	Typical value

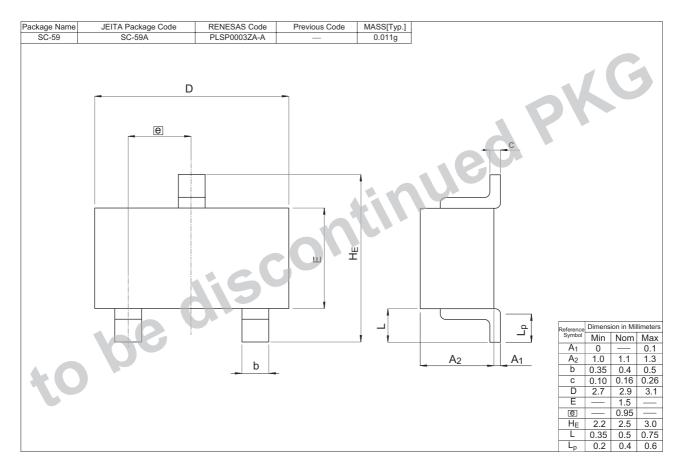
Notes: 1. With gate to cathode resistance  $R_{GK}$  = 1  $k\Omega$ .

#### **Electrical Characteristics**

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak reverse current	I <sub>RRM</sub>	_	_	0.1	mA	Tj = 125°C, V <sub>RRM</sub> applied
Repetitive peak off-state current	$I_{DRM}$	_	_	0.1	mA	Tj = 125°C, V <sub>DRM</sub> applied,
						$R_{GK} = 1 k\Omega$
On-state voltage	$V_{TM}$	_	_	1.9	V	Ta = 25°C, I <sub>TM</sub> = 1.5 A,
						instantaneous value
Gate trigger voltage	$V_{GT}$	_	_	0.8	V	$Tj = 25$ °C, $V_D = 6 V$ , $I_T = 0.1 A$
Gate non-trigger voltage	$V_{\sf GD}$	0.2	_	_	V	$Tj = 125$ °C, $V_D = 1/2 V_{DRM}$ ,
						$R_{GK} = 1 k\Omega$
Gate trigger current	I <sub>GT</sub>	20	_	100	μΑ	$Tj = 25$ °C, $V_D = 6 V$ , $I_T = 0.1 A$
Holding current	I <sub>H</sub>	_	_	3.0	mA	$Tj = 25^{\circ}C, V_D = 12 V,$
						$R_{GK} = 1 k\Omega$
Thermal resistance	R <sub>th (j-a)</sub>	_	_	500	°C/W	Junction to ambient

#### **Package Dimensions**





#### CR05BS-8

#### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example	
Surface-mounted type	Taping	3000	Type name – ET +Direction (1 or 2) +3	CR05BS-8-ET13	

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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#### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510